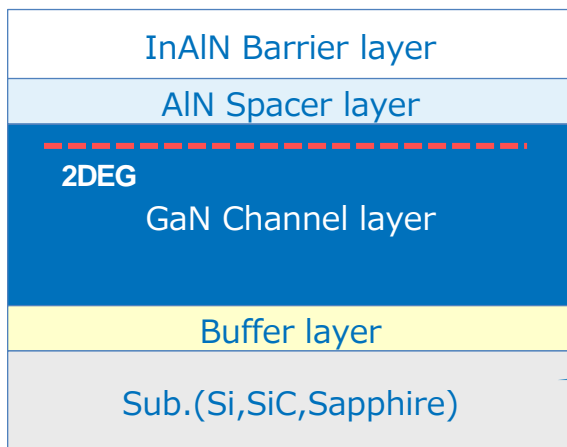


# InAlN / GaN HEMT

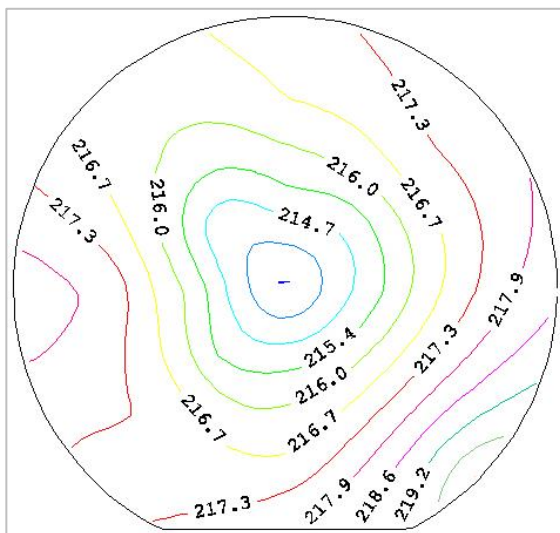
For next generation high frequency and high output power devices

## ■ Typical Structure



Si: up to **8** inch  
 SiC: up to **4** inch  
 Sapphire: up to **3** inch

## ■ Sheet resistivity distribution on 6 inch InAlN/GaN HEMT and hall effect



Ave.: 216 ohm/sq. (Var.: 3.6%)

### Hall

Rs [ohm/sq.]	219
$\mu$ [cm <sup>2</sup> /Vs]	1300
Ns[cm <sup>-2</sup> ]	2.20e13

\*Some of the specifications may change without prior notice.

For Further Inquiry [https://keytech.ntt-at.co.jp/en/epi/prd\\_1002.html](https://keytech.ntt-at.co.jp/en/epi/prd_1002.html)

